

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI HF15-28S is Designed for

FEATURES:

-
-
- **Omnigold™** Metalization System

MAXIMUM RATINGS

| | |
|-------------------------|-------------------------------|
| I_C | 4.0 A |
| V_{CB0} | 65 V |
| V_{CEO} | 35 V |
| V_{EBO} | 4.0 V |
| P_{DISS} | 40 W @ T _C = 25 °C |
| T_J | -65 °C to +200 °C |
| T_{STG} | -65 °C to +150 °C |
| q_{JC} | 4.4 °C/W |

PACKAGE STYLE .380 4L STUD

| DIM | MINIMUM inches / mm | MAXIMUM inches / mm |
|-----|------------------------|------------------------|
| A | .220 / 5.59 | .230 / 5.84 |
| B | .980 / 24.89 | |
| C | .370 / 9.40 | .385 / 9.78 |
| D | .004 / 0.10 | .007 / 0.18 |
| E | .320 / 8.13 | .330 / 8.38 |
| F | .100 / 2.54 | .130 / 3.30 |
| G | .450 / 11.43 | .490 / 12.45 |
| H | .090 / 2.29 | .100 / 2.54 |
| I | .155 / 3.94 | .175 / 4.45 |
| J | | .750 / 19.05 |

ORDER CODE: ASI10603

CHARACTERISTICS T_C = 25 °C

| SYMBOL | TEST CONDITIONS | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|-------------------------|--|---------|---------|---------|-------|
| BV_{CEO} | I _C = 200 mA | 35 | | | V |
| BV_{CES} | I _C = 200 mA | 65 | | | V |
| BV_{EBO} | I _E = 10 mA | 4.0 | | | V |
| I_{CB0} | V _{CB} = 30 V | | | 2.0 | mA |
| h_{FE} | V _{CE} = 5.0 V I _C = 200 mA | 5.0 | | --- | --- |
| C_{OB} | V _{CB} = 30 V f = 1.0 MHz | | | 50 | pF |
| G_P | V _{CE} = 28 V f = 150 MHz | 10 | | --- | dB |
| f_T | V _{CE} = 10 V I _C = 200 mA f = 100 MHz | 250 | | | MHz |